Amendments to the Specification

Please replace the paragraph at page 6, line 23 to page 7, line 6 with the following amended paragraph:

Recall Figure 1 and the fact that this design poses a number of problems in terms of the impedances seen from the common port of the microstrip line 6 when the various ports 1-4 are switched on. One solution to this problem is shown in Figures 2a and 2b. The structure of Figures 2a and 2b preferably consists of a multi-layer printed circuit board 12, on which a common RF line 14 is formed on the bottom or back side 13 of the board 12, and is fed through a ground plane 18 by a metal plated via 20 to a central point 7 in the center of a 1x4 switch matrix of switches 10-1 through 10-4, which switches may be made as a hybrid on a common substrate (not shown) or which may be individually attached to surface 9. Switches 10-1 through 10-4 comprise a set of RF MEMS switches 10 (the numeral 10 when used without a dash and another numeral is used herein to refer to these RF MEMS switches in general as opposed to a particular switch). As will be seen, the number of switches 10 in the set can be greater than four, if desired.

Please replace the paragraph at page 9, line 23 to page 10, line 3 with the following amended paragraph:

In Figures 2a and 3a the DC control lines 11 and 22 are depicted as being thinner than are the RF lines 1-4. If the DC lines are much thinner than the RF lines, they will have a higher impedance and coupling with the RF lines will be thereby reduced. While the percentage by which the DC are made thinner than the RF lines is somewhat a matter of tradeoffs, it is believed their width should preferably be

about 25% of the width of the RF lines or less. The DC lines should be separated by at least one RF line width from the RF lines to reduce unwanted coupling. The MEMS switches may be wired to their RF lines, DC control lines, ground pads or lines by means of wires [[13]]30 bonded to the respective switches 10 and their various lines and/or pads.

Please replace the paragraph at page 10, lines 15-17 with the following amended paragraph:

In the embodiment of Figures 5a and 5b, all of the DC bias lines 11 pass through metal plated vias 21, 26. Half of them contact the ground plane 18 and the other half pass through the ground plane to contact traces 27 on the bottom or back side 13 of the board 12.

Please replace the paragraph at page 12, line 27 to page 13, line 15 with the following amended paragraph:

Each flared notch 37 is fed by a separate microstrip line 1-4, each of which crosses over the notch of an antenna and is shorted to the ground plane 18 (see, e.g., Figure 5b) on the opposite side of board 12 at vias 39. These microstrip lines correspond to the similarly numbered ports 1-4 discussed with respect to the switch arrangements of the earlier mentioned figures. RF energy passing down these microstrip lines is radiated from the associated antenna structure in a direction that antenna is pointing (i.e. along the mid-points of the notch of the notch antenna which is excited). The DC bias lines 11 and 11a are preferably routed to a common connector [[41]]42 on the bottom side of the board 12 and the RF input preferably comprises a single feed point [[42]]41 which is routed to

one of the four antenna structures (by means of one of the microstrips 1-4) as determined by which MEMS switch 10 (see FIG. 5a the switches 10 are too small to be shown clearly on Figure 7, but they are clustered around point 7) is closed. Bias lines 11 are disposed on the top side of board 12 while bias lines 11a are disposed on the bottom side thereof. They are coupled together through the board 12 by means of vias. A pad 8 of one via is numbered in FIG. 7 (the other vias are unnumbered due to the limited space available around them for reference numerals, but the vias can, nevertheless, be easily seen). The vias in Figure 7 are shown spaced further from the center point 7 than they would be in an actual embodiment, merely for ease of illustration.